

	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 5665620 A	19970909	8	Method for forming concurrent top oxides using reoxidized silicon in an EPROM	438/593	438/265; 438/266; 438/594	Nguyen, Bich-Yen et al.
2	US 6319775 B1	20011120	7	Nitridation process for fabricating an ONO floating-gate electrode in a two-bit EEPROM device	438/261	438/763	Halliyal, Arvind et al.
3	US 6180538 B1	20010130	7	Process for fabricating an ONO floating-gate electrode in a two-bit EEPROM device using rapid-thermal-chemical-vapor-deposition	438/769	438/786	Halliyal, Arvind et al.
4	US 5856223 A	19990105	11	Method for manufacturing self-aligned split-gate flash memory cells	438/264	438/266	Wang, Lin-Song